

INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.3101	Serial No.
Applicant	Koji USUDA et al.	
Filing Date	July 28, 2003	Group:

U.S. PATENT DOCUMENTS							
Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS							
		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
PC	McKee et al. "PHYSICAL STRUCTURE AND INVERSION CHARGE AT A SEMICONDUCTOR INTERFACE WITH A CRYSTALLINE OXIDE", Science, Vol. 293, pages 468-471, (2001)
PC	Nishikawa et al., "DIRECT GROWTH OF SINGLE CRYSTALLINE CeO ₂ HIGH-K GATE DIELECTRICS", Extended Abstracts of the 2001 International Conference on Solid State Devices and Materials, pages 174-175, (2001)
PC	Gottschalk et al., "EPITAXIAL Pr ₂ O ₃ ON SILICON AS AN ALTERNATIVE GATE OXIDE FOR FUTURE CMOS APPLICATIONS", JOINT SESSION CRYSTALLINE OXIDES FOR GATE DIELECTRICS, Session N8.5/T6.5, pages 350-351, (2002)
PC	Tezuka et al., "NOVEL FULLY-DEPLETED SiGe-ON-INSULATOR pMOSFETs WITH HIGH-MOBILITY SiGe SURFACE CHANNELS", IEDM Tech. Dig., 946, IEEE, (2001)
PC	Welser et al.; "STRAIN DEPENDENCE OF THE PERFORMANCE ENHANCEMENT IN STRAINED-Si <i>n</i> -MOSFETs"; IEDM, pages, 373-376, IEEE, (1994)
PC	Hirose et al.; "FUNDAMENTAL LIMIT OF GATE OXIDE THICKNESS SCALING IN ADVANCED MOSFETs"; Semicond. Sci. Technol. Vol. 15, pages 485-490, (2000)

Examiner	PHAT X - CAO	Date Considered	10/21/04
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OMB No. 0651-0011

INFORMATION DISCLOSURE CITATION

Atty. Docket No. 04329.3101-01	Div. of Appln. No. 10/627,648
Applicant Koji USUDA, et al.	
Filing Date August 9, 2004	Prior Group: 2814

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
PC	2003-234472	08/2003	Japan			No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner PHAT X- CAD	Date Considered 10/21/04
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Applicant	Koji USUDA, et al.		
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PC	Hirose et al.; "FUNDAMENTAL LIMIT OF GATE OXIDE THICKNESS SCALING IN ADVANCED MOSFETs"; Semicond. Sci. Technol. Vol. 15, pages 485-490, (2000)

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